

TOSHIBA BiCD Digital Integrated Circuit Silicon Monolithic

# TB62752AFUG

Step Up Type DC/DC Converter for White LED

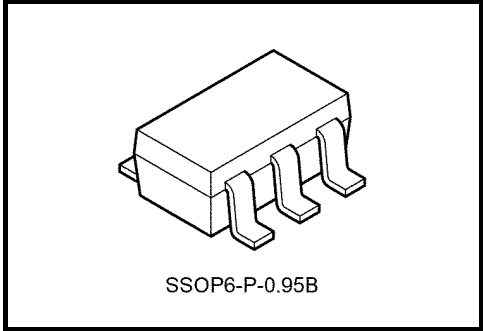
**Features**

The TB62752AFUG is a high efficient Step-Up Type DC/DC Converter specially designed for constant current driving of White LED.

This IC can drive 2-8 white LEDs connected series using a Li-ion battery.

This IC contains N-ch MOS-FET Transistor for Coil-Switching, and LED Current ( $I_F$ ) is set with an external resistor.

This IC is especially for driving back light white LEDs in LCD of PDA, Cellular Phone, or Handy Terminal Equipment.

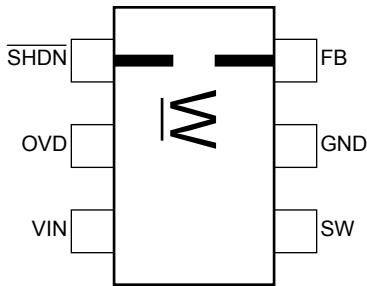


Weight: 0.016 g (Typ.)

**Characteristics**

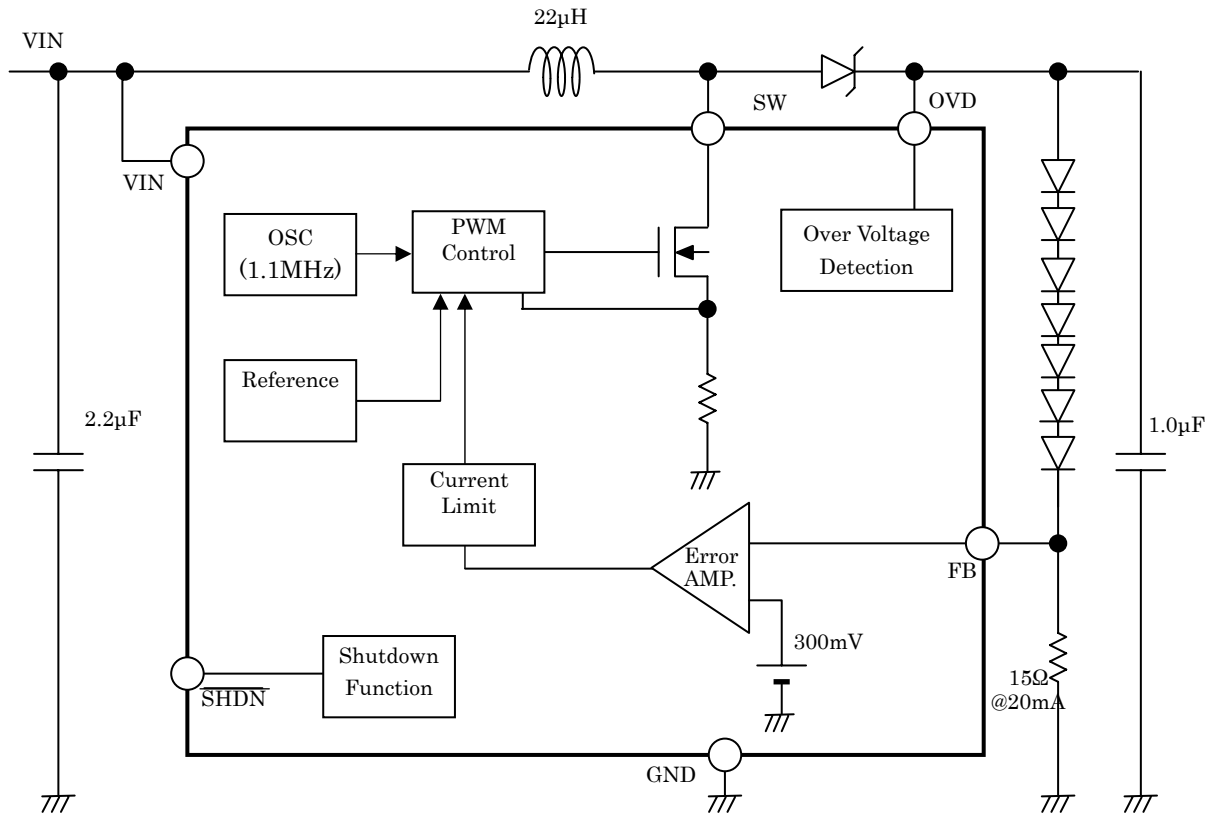
- 2-8 white LEDs connected series (Typ. 7LEDs)
- Variable LED Current  $I_F$  is set with a external resistor :  
20 mA (Typ.) @RSENS = 15  $\Omega$
- Output Power : Available for 800mW LED loading
- High Efficiency : 80% over (Using recommended external parts: Typ. 7LEDs)
- Output Over Voltage Shutdown Function :  
Switching Operation is shut downed when OVD terminal Voltage is over 37 V (typ.).
- IC Package : SSOP6=p=0.95B
- Switching Frequency : 1.1 MHz (Typ.)

**Pin Assignment (Top view)**



**Caution 1:** This IC could be destroyed in some case if amounted in 180° inverse direction.  
Please be careful about IC direction in mounting.

**Block Diagram**



**Pin Function**

Pin No.	Symbol	Function Description
1	SHDN	Voltage-Input Terminal for IC-Enable / Disable LED- $I_F$ . $I_F$ adjustment with PWM input signal is also available.
2	OVD	Over Voltage Detection Terminal. IC Switching Operation is disabled with detection over voltage. If the voltage returns to detection level or less, Operation is enabled again.
3	VIN	Supply Voltage Input Terminal. ( 2.8V to 5.5V)
4	SW	Switch Terminal for DC/DC Converter. Nch MOSFET Built-In.
5	GND	Ground Terminal.
6	FB	LED $I_F$ Setting Resistor Connecting Terminal.

## Absolute Maximum Ratings (Topr = 25 °C if without notice)

Characteristics	Symbol	Ratings	Unit
Power Supply Voltage	VIN	-0.3 to +6.0	V
Input Voltage	VSHDN	-0.3 to +VIN + 0.3	V
Switching Terminal Voltage	Vo (SW)	-0.3 to 40	V
Switching Terminal Current	Io (SW)	1500	mA
Power Dissipation	PD	0.41 (Device)	W
		0.47 (on PCB) Caution 2	
Thermal Resistance	Rth (j-a)	300 (Device)	°C/W
		260 (on PCB)	
Operation Temperature Range	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Maximum Junction Temperature	Tj	150	°C

Caution 2: Power Dissipation must be calculated with subtraction of 3.8 mW/°C from Maximum Rating with every 1°C if T<sub>opr</sub> is upper 25°C. (on PCB)

## Recommended Operating Condition (Ta = -40°C to 85°C if without notice)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Typ	Max	Unit
Power Supply Voltage	VIN	-		2.8	-	5.5	V
LED Current (Average Value)	Io1	-	VIN = 3.6 V, RSENS=15Ω 4LEDs, Topr = 25°C	-	20	-	mA

## Electrical Characteristics (Ta = 25°C, VIN=2.8V to 5.5V if without notice)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Input Voltage Range	VIN		2.8	-	5.5	V
Operating Consumption Current	IIN (On)	VIN=3.6V, RSENS=15Ω	-	TBD	-	mA
Quiescent Consumption Current	IIN (Off)	VIN=3.6V, VSHDN=0V	-	0.5	1.0	μA
SHDN Terminal 'H' Level Input Voltage	VSHDNH	-	1.3	-	VIN	V
SHDN Terminal 'L' Level Input Voltage	VSHDNL	-	0	-	0.4	V
SHDN Terminal Current	ISHDN	VIN=3.6V, VSHDN=3.6V	-	0	1.0	μA
Integrated MOS-Tr Switching Frequency	fOSC	VIN=3.6V, VSHDN=3.6V	0.77	1.1	1.43	MHz
Switching Terminal Current	IoZ (SW)	-	-	600	-	mA
Switching Terminal Leak Current	IoZ (SW)	-	-	0.5	1	μA
FB Terminal Feedback Voltage (VFB)	VFB	VIN=3.6V, RSENS=15Ω Topr=25°C, L=22μH	285	300	315	mV
FB Terminal Line Regulation	ΔVFB	VIN=3.6V center VIN=3.0 to 5.0V	-5	-	5	%
FB Terminal Current	IoZ (SW)	-	-	TBD	-	μA
OVD terminal Voltage	VOVD	-	34.5	37	39.5	V
OVD Terminal Leakage Current	IOVDZ	VOVD=30V	-	0.5	1	μA

## Protection in LED opened condition

The operation with OVD terminal is available for the protection in case LED Circuit opened.

Please see the example of application circuit.

If load of LED is detached, Nch MOS switching operation is disabled with detection of boost circuit voltage.

## Setting of external Capacitor

In case not using PWM signal to  $\overline{\text{SHDN}}$  terminal for brightness control, recommended values are

$C_1 = \text{Over } 2.2 (\mu\text{F}), C_2 = \text{Over } 1.0 (\mu\text{F})$

In case with PWM signal to  $\overline{\text{SHDN}}$  terminal for brightness control, recommended values are

$C_1 = \text{Over } 4.7 (\mu\text{F}), C_2 = \text{Under } 0.1 (\mu\text{F})$  to reduce fluctuation of input current and up accuracy of brightness.

The recommended capacitor values depend on the Brightness Control Method.

<Please see after page-8>

The capacitor value must be considered for gain enough accuracy of brightness with reduction of noise from Input current changing.

## Setting of $I_o$

Resistance connects between RSENS pin and GND.

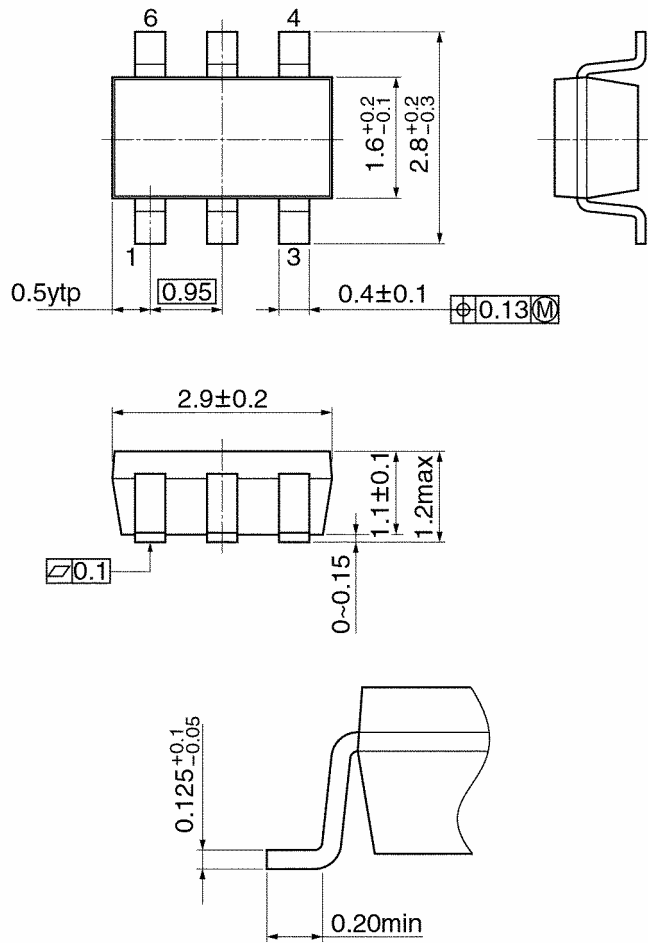
The average current is set by this RSENS value and average current are obtained by the following equation.

$$I_F[\text{mA}] = \frac{300[\text{mV}]}{\text{RSENS} [\Omega]}$$

Current Value error is within  $\pm 5\%$ .

Package Dimensions  
SSOP6-P-0.95B

Unit: mm



Weight : 0.016 g (Typical)

About solderability, following conditions were confirmed

- Solderability

- (1) Use of Sn-63Pb solder Bath

- solder bath temperature = 230°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux

- (2) Use of Sn-3.0Ag-0.5Cu solder Bath

- solder bath temperature = 245°C
    - dipping time = 5 seconds
    - the number of times = once
    - use of R-type flux

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